

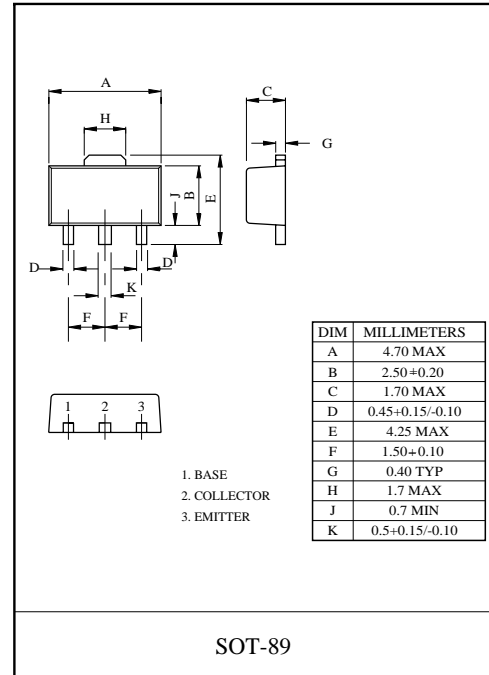
PNP Transistor

FEATURES

- High current applications
- Complementary to FTC4375

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-30	V
V _{CEO}	Collector-Emitter Voltage	-30	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1.5	A
P _C	Collector Power Dissipation	500	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

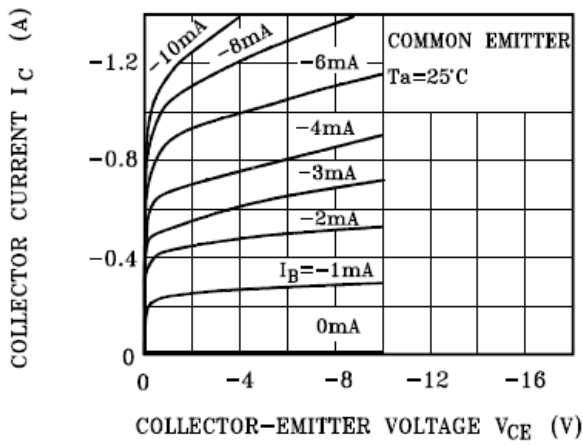
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V, I _C =-0.5A	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1.5A, I _B =-30mA			-2	V
Base-emitter voltage	V _{BE}	V _{CE} =-2V, I _C =-0.5A			-1	V
Transition frequency	f _T	V _{CE} =-2V, I _C =-500mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			50	MHz

CLASSIFICATION OF h_{FE(1)}

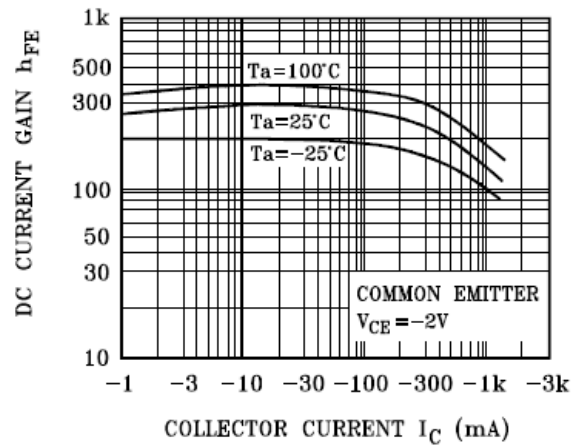
Rank	O	Y
Range	100-200	160-320
Marking	HO	HY

Typical Characteristics

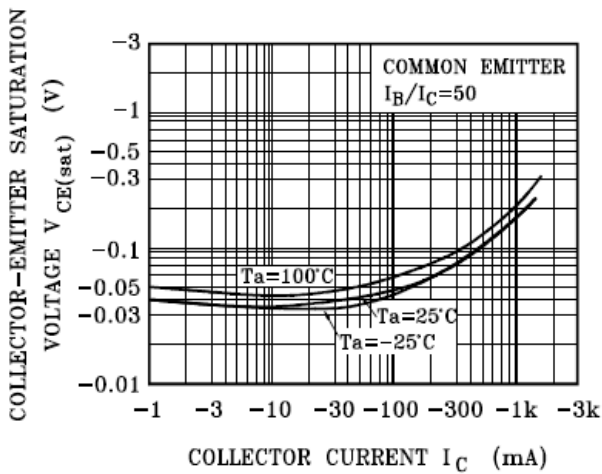
$I_C - V_{CE}$



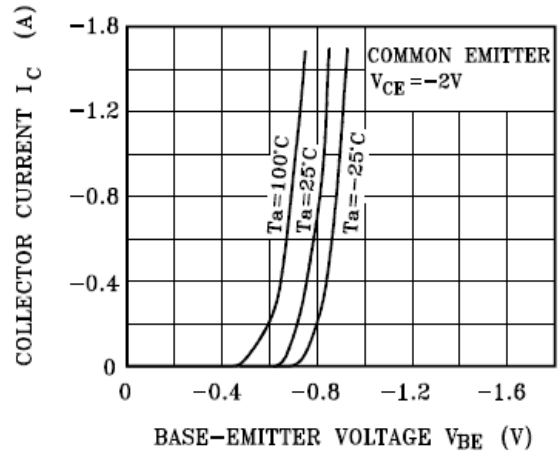
$h_{FE} - I_C$



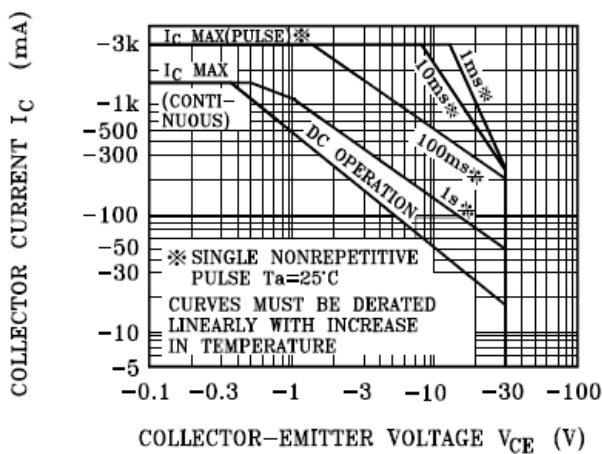
$V_{CE(sat)} - I_C$



$I_C - V_{BE}$



SAFE OPERATING AREA



$P_C - T_a$

